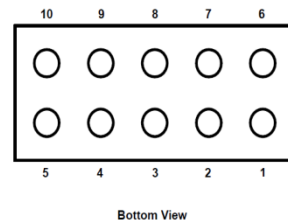
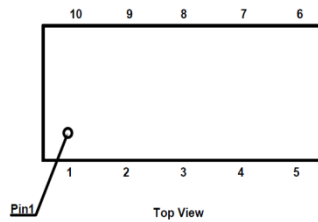
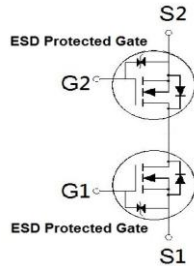




**PRODUCT SUMMARY**

$V_{(BR)SSS}$	$R_{SS(ON)}$	$I_S$
30V	7.8mΩ	14A



1,2,4,5 : Source1  
3 : Gate1  
8 : Gate2  
6,7,9,10 : Source2

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Source-Source Voltage	$V_{SSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Source Current	$I_S$	14	A
Pulsed Source Current <sup>1</sup>	$I_{SP}$	70	
Total Dissipation	$P_T$	2.5	W
Thermal Resistance <sup>1</sup>	$R_{\theta JA}$	50	$^\circ\text{C} / \text{W}$
Operating Junction & Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$

<sup>1</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ , Unless Otherwise Noted)**

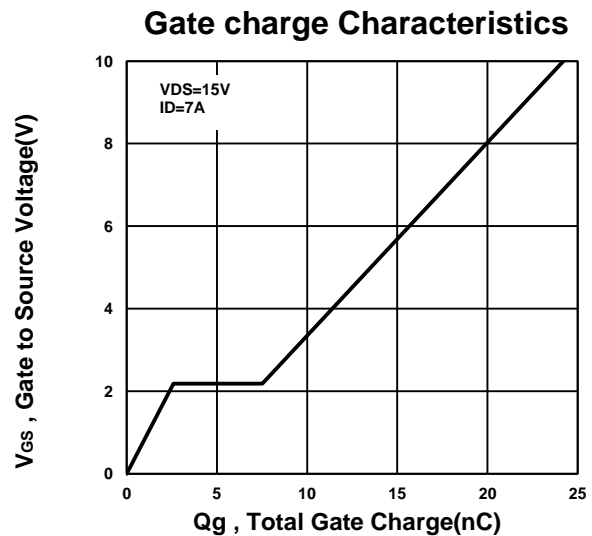
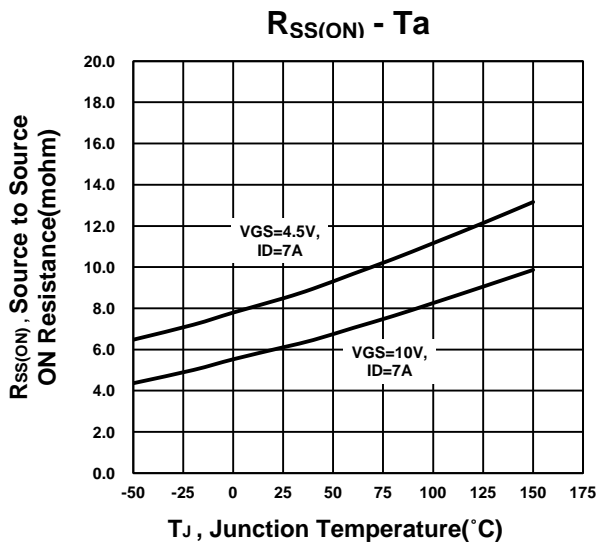
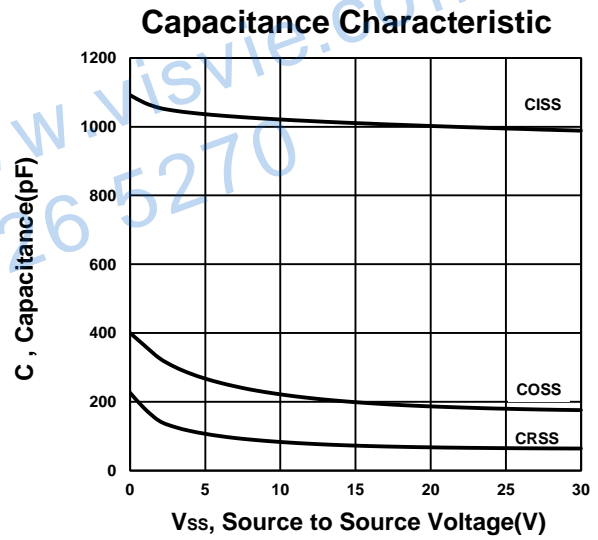
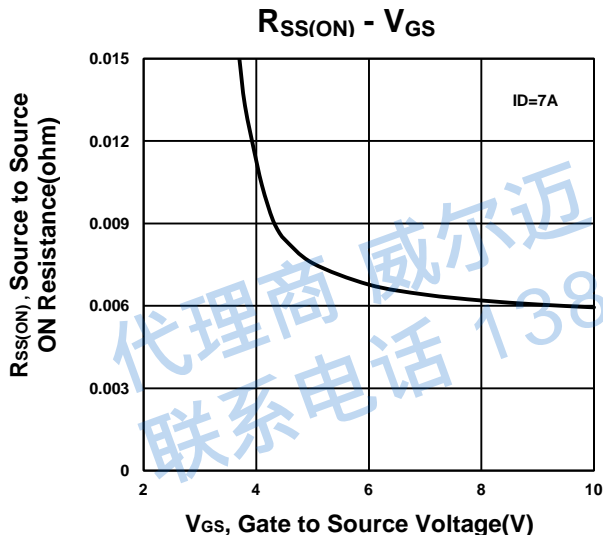
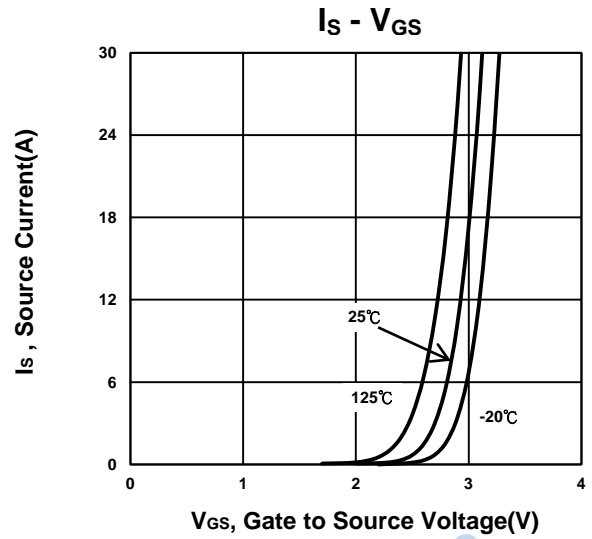
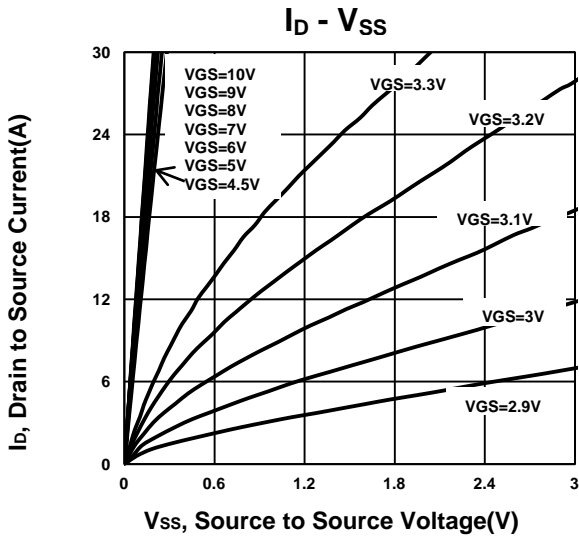
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Source-Source Breakdown Voltage	$V_{(BR)SSS}$	$V_{GS} = 0V, I_S = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = 10V, I_S = 250\mu\text{A}$	1.3	1.8	2.3	
Gate-Source Leakage	$I_{GSS}$	$V_{SS} = 0V, V_{GS} = \pm 20V$			$\pm 10$	$\mu\text{A}$
Zero Gate Voltage Source Current	$I_{SSS}$	$V_{SS} = 30V, V_{GS} = 0V$			1	$\mu\text{A}$
Source-Source On-State Resistance <sup>1</sup>	$R_{SS(ON)}$	$V_{GS} = 10V, I_S = 7A$		6.2	7.8	mΩ
		$V_{GS} = 4.5V, I_S = 7A$		8.5	11	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{SS} = 5V, I_S = 7A$		45		S

DYNAMIC					
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$	1011		pF
Output Capacitance	$C_{oss}$		198		
Reverse Transfer Capacitance	$C_{rss}$		72		
Total Gate Chang <sup>2</sup>	$Qg$	$V_{SS} = 15V, V_{GS} = 10V$ $I_S = 7A$	24		nC
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{SS} = 15V,$ $I_S \cong 7A, V_{GS} = 10V$	0.43		uS
Rise Time <sup>2</sup>	$t_r$		0.61		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$		1.33		
Fall Time <sup>2</sup>	$t_f$		0.85		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ )					
Forward Source-Source Voltage <sup>1</sup>	$V_F$	$I_S = 7A, V_{GS} = 0V$	0.72	1.2	V

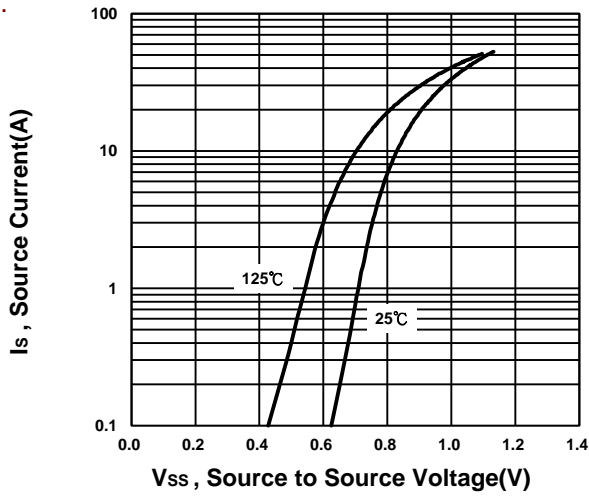
<sup>1</sup>Pulse test : Pulse Width  $\leq 300\text{ }\mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup>Independent of operating temperature.

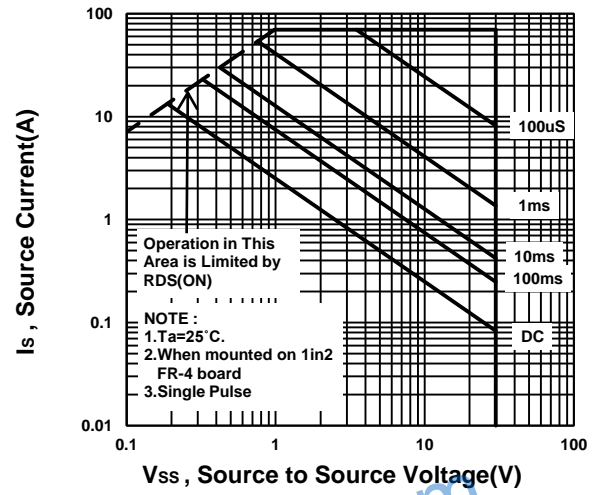
代理商 威尔迈 [www.visvie.com](http://www.visvie.com)  
联系电话 138 2526 5270



$I_S - V_F$



Safe Operating Area



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